

IMPROVED FIELD-EFFECT TRANSISTOR AND CORRESPONDING MANUFACTURING METHOD

ABSTRACT

5 A field effect transistor having a variable doping profile is presented. The field effect transistor is integrated on a semiconductor substrate with a respective active area of the substrate including a source and drain region. A channel region is interposed between the source and drain regions and has a predefined nominal width. The effective width of the channel region is defined by a variable doping profile.

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